

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		ATTY. DOCKET NO. 33035M0341	SERIAL NO. To Be Assigned
		APPLICANTS: Kensaku Motoki, et al.	
		FILING DATE Herewith	GROUP ART UNIT To Be Assigned

U.S. Patent Documents

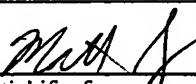
Examiner Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
M)	AA	4,727,047	2/1988	Bozler, et al.	—	—	
	AB	6,225,650	5/2001	Tadatomo et al.	—	—	
	AC	5,843,227	12/1998	Kimura et al.	—	—	
	AD	5,846,609	12/1998	Shiralagi	—	—	
	AE	6,087,681	7/2000	Shakuda	—	—	
	AF	6,096,130	8/2000	Kimura	—	—	
M)	AG	6,156,581	12/2000	Vaudo et al.	—	—	

FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO
M)	AD	09-194299	7/29/97	Japan			Abstract
	AE	8-116090	5/7/96	Japan			Abstract
	AF	9-255496	9/30/97	Japan			Abstract
	AG	7-273048	10/20/95	Japan			Abstract
	AH	51-50899	5/4/76	Japan			X
	AI	10-265297	10/6/98	Japan			Abstract
	AJ	10-312971	11/24/98	Japan			Abstract
	AK	10-326751	12/8/98	Japan			Abstract
	AL	10-321529	12/4/98	Japan			X
M)	AM	09-255496	9/30/97	Japan			Abstract

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

AN	
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EXAMINER 	DATE CONSIDERED 3/31/2005
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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	AA						
	AB						

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	AC						
	AD						

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

	AE	Chinese Office Action mailed June 20, 2003.
MS	AF	U. Akira et al. "Thick GaN Epitaxial Growth With Low Dislocation Density by Hydride Vapor Phase Epitaxy" Japanese Journal of Applied Physics, 15 July 1997, Part. 2, Vol. 36, No. 7B, pp. L899-L902.
MM	AG	S. Akira et al. "Defect Structure in Selectively Grown GaN Films With Low Threading Dislocation Density" Applied Physics Letters, 20 October 1997, Vol. 71, No. 16, pp. 2259-2261.
MS	AH	H. Shima et al. "Selective Growth of GaN on Submicron Pattern by MOVPE (in Japanese)" Technical Report of IEICE, Vol. 97, No. 61, 23 May 1997 (Tokyo), pp. 41-46.
MM	AI	T. Shibata et al. "Preparation of High-Quality GaN Bulk Single Crystal by Selective HVPE Growth (in Japanese)", Technical Report of IEICE, Vol. 97, No. 61, 23 May 1997 (Tokyo), pp. 35-40.
MM	AJ	K. Shota et al. "Fabrication of GaN Hexagonal Pyramids on Dot-Patterned GaN/Sapphire Substrates Via Selective Metalorganic Vapor Phase Epitaxy" Japanese Journal of Applied Physics, 15 September 1995, Part 2, Vol. 34, No. 9B, pp. L1184-L1186.
MM	AK	International Preliminary Examination Report (PCT/IPEA/409) (translated) for J PCT/JP98/04908.
MM	AL	International Search Report for PCT/JP98/04908.
MM	AM	Cover page of WO99/23693.
MM	AN	Forms PCT/IB/304 and PCT/IB/308.
MD	AO	Korean Office Action mailed April 23, 2003

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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		ATTY. DOCKET 33035M0341	SERIAL NO. 10/691,540
		Applicant Kensaku Motoki, et al.	
		FILING DATE October 24, 2003	GROUP ART UNIT 1765

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*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
MS	AA	5,970,314	10/19/99	Okahisa, et al.	—	—	
MS	AB	5,962,875	10/5/99	Motoki, et al.	—	—	
MS	AC	5,834,325	11/10/98	Motoki, et al.	—	—	

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*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO
MS	AD	WO 96/41906	12/27/96	PCT	—	—	
MS	AE	EP 0 801 156	10/15/97	EPO	—	—	
MS	AF	EP 0 810 674	12/3/97	EPO	—	—	

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MS	AG	Masaki Nagahara, et al., "Selective Growth of Cubic GaN in Small Areas on Patterned GaAs (100) Substrates by Metalorganic Vapor Phase Epitaxy", Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Vol. 33, No. 1B, Part 1, (1994), pp. 694-697, XP000596419
MS	AH	X. Li, et al., "Characteristics of GaN Stripes Grown by Selective-Area Metalorganic Chemical Vapor Deposition", Journal of Electronic Materials, Vol. 26, No. 3, (1996), pp. 306-310, XP009004611
MS	AI	Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Matsushima H. et al., "Sub-micron fine structure of GaN by metalorganic vapor phase epitaxy (MOVPE) selective area growth (SAG) and buried structure by epitaxial lateral overgrowth (ELO)", Database accession no. 6037425 XP-002268861
MS	AJ	Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Shibata T et al., "Hybrid vapor-phase epitaxy growth of high-quality GaN bulk single crystal by epitaxial lateral overgrowth", Database accession no. 6037423 XP-002268862
MS	AK	Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Sasaoka C et al., "High-quality InGaN MQW on low-dislocation-density GaN substrate grown by hydride vapor-phase epitaxy", Database accession no. 6037422 XP-002268863

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